

CMFD2004i

**SURFACE MOUNT
DUAL ISOLATED HIGH VOLTAGE
SILICON SWITCHING DIODES**

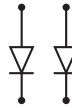


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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMFD2004i consists of two electrically Isolated high voltage switching diodes packaged in an epoxy molded SOT-143 surface mount case. This device is designed for switching applications requiring dual high voltage diodes.

MARKING CODE: CJP



SOT-143 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Peak Repetitive Reverse Current
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_R	240
V_{RRM}	300
I_O	200
I_F	225
I_{FRM}	450
I_{FSM}	4.0
I_{FSM}	1.0
P_D	350
T_J, T_{stg}	-65 to +150
θ_{JA}	357

UNITS

V
V
mA
mA
mA
A
A
mW
$^\circ\text{C}$
$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

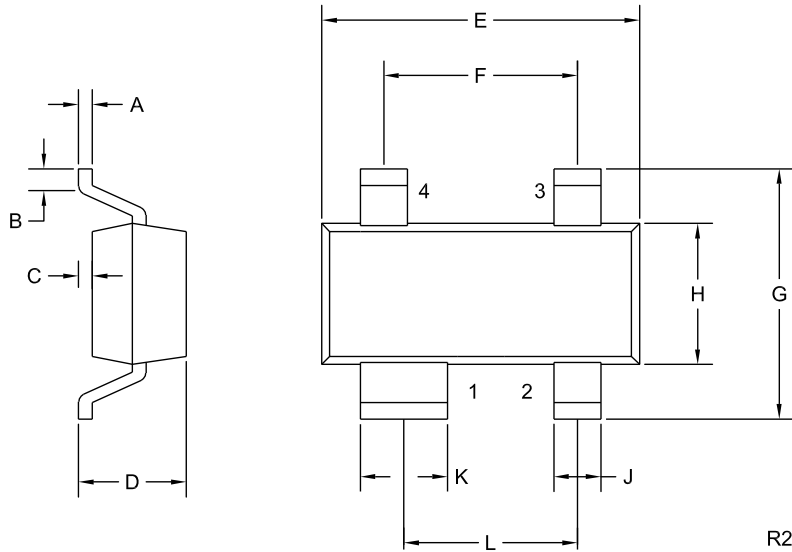
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=240\text{V}$		100	nA
I_R	$V_R=240\text{V}, T_A=150^\circ\text{C}$		100	μA
BV_R	$I_R=100\mu\text{A}$	300		V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0, f=1.0\text{MHz}$		5.0	pF
t_{rr}	$I_F=I_R=30\text{mA}, I_{rr}=3.0\text{mA}, R_L=100\Omega$		50	ns

R5 (13-August 2010)

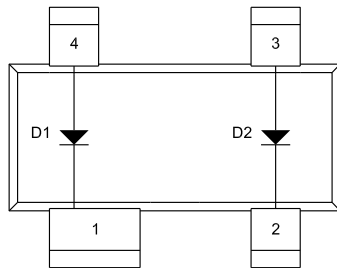
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SILICON SWITCHING DIODES



SOT-143 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Cathode D1
- 2) Cathode D2
- 3) Anode D2
- 4) Anode D1

MARKING CODE: CJP

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.006	0.08	0.15
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	-	0.045	-	1.14
E	0.110	0.120	2.79	3.04
F	0.075		1.90	
G	-	0.098	-	2.50
H	0.047	0.055	1.19	1.40
J	0.014	0.020	0.36	0.50
K	0.030	0.037	0.76	0.93
L	0.067		1.70	

SOT-143 (REV: R2)

R5 (13-August 2010)